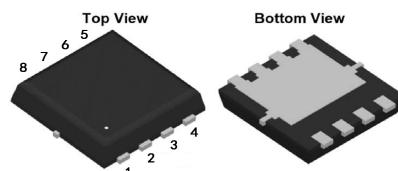


30V N-Channel Mosfet

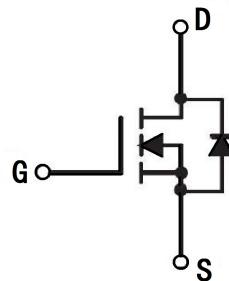
FEATURES

- $R_{SS(ON)}=14\text{m}\Omega(\text{Typ.}) @ V_{GS}=10\text{V}$
- $R_{SS(ON)}=25\text{m}\Omega(\text{Typ.}) @ V_{GS}=4.5\text{V}$

PDFN3.3*3.3-8L**APPLICATIONS**

- Portable appliances
- Power management

1: S	3: S	5: D	7: D
2: S	4: G	6: D	8: D

MARKING**N-CHANNEL MOSFET**

YYMM:Date Code(year & month)

MAXIMUM RATINGS ($T_c=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter		Limit	Units
V_{DS}	Drain-Source Voltage		30	V
V_{GS}	Gate-Source Voltage		± 20	V
I_D	Continuous Drain Current ^{note1}	$T_c = 25^\circ\text{C}$	30	A
		$T_c = 100^\circ\text{C}$	20	A
I_{DM}	Pulsed Drain Current ^{note2}		120	A
P_D	Power Dissipation		36	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		3.5	$^\circ\text{C}/\text{W}$
T_J	Junction Temperature		150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range		-55 to +150	$^\circ\text{C}$

MOSFET ELECTRICAL CHARACTERISTICS $T_c=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu\text{A}$	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24V, V_{GS} = 0V$	-	-	1	μA
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	± 100	nA
On Characteristics						
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	1.0	1.6	2.5	V
$R_{DS(\text{ON})}$	Gate Drain-Source On-State Resistance <small>note3</small>	$V_{GS}=10V, I_D=5A$	-	14	23	$\text{m}\Omega$
		$V_{GS}=4.5V, I_D=3A$	-	25	39	
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = 15V, V_{GS} = 0V, f = 1.0\text{MHz}$	-	1397	-	pF
C_{oss}	Output Capacitance		-	425	-	pF
C_{rss}	Reverse Transfer Capacitance		-	164	-	pF
Q_g	Total Gate Charge	$V_{DS}=15V, V_{GS}=10V, I_D=10A$	-	17	-	nC
Q_{gs}	Gate-Source Charge		-	2.8	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	3.5	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{DS}=15V, I_D=10A$ $V_{GS} = 10V, R_G = 4\Omega$	-	15	-	ns
t_r	Turn-On Rise Time		-	9	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	32	-	ns
t_f	Turn-Off Fall Time		-	8	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current	-	-	30	A	
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	120	A	
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0V, I_{SD}=10A,$	-	-	1.2	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0V, I_F=10A,$	-		40	ns
Q_{rr}	Reverse Recovery Charge	$di/dt = 100\text{A}/\mu\text{s}$	-		22	nC

Notes: 1. Calculated continuous current based on maximum allowable junction temperature.

2 . Repetitive rating; pulse width limited by max. junction temperature.

3 . Pulse Test: Pulse Width $\leq 380\mu\text{s}$, Duty Cycle $\leq 2\%$

Typical Performance Characteristics

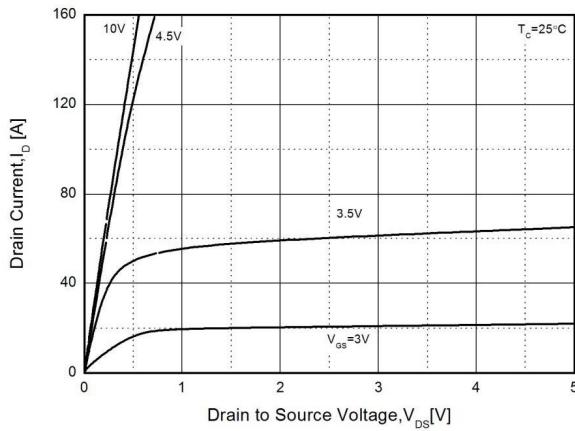


Figure1. Output Characteristics

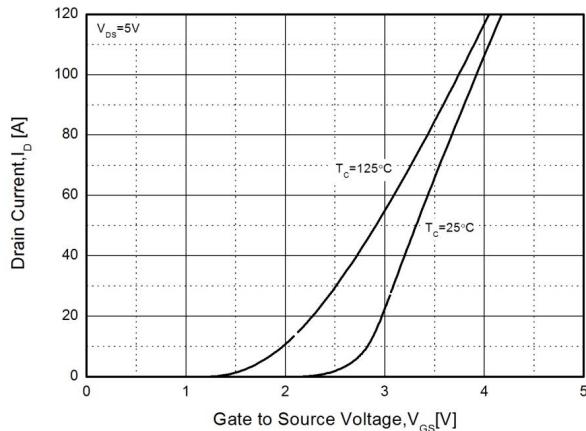


Figure2. Transfer Characteristics

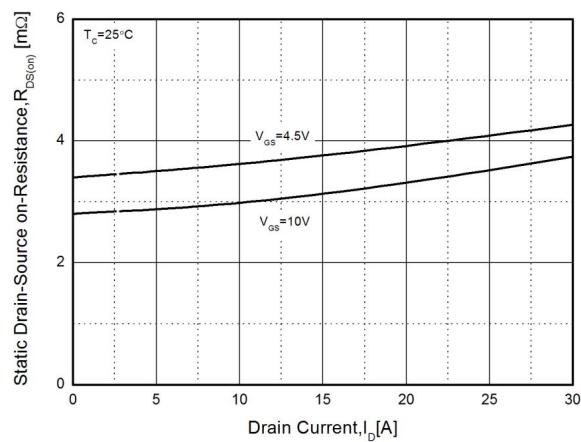


Figure3. $R_{DS(on)}$ -Drain Current

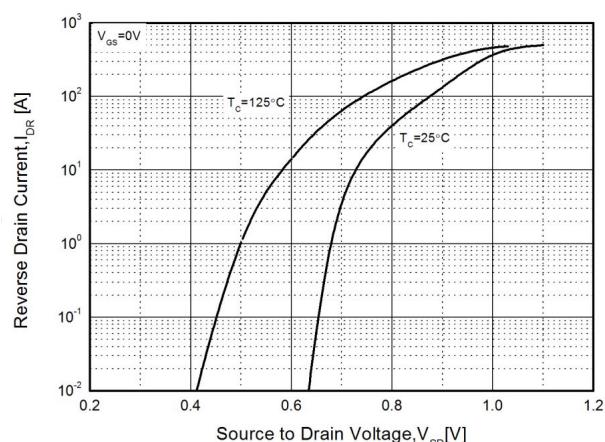


Figure4. Typical Source-Drain Diode Forward Voltage

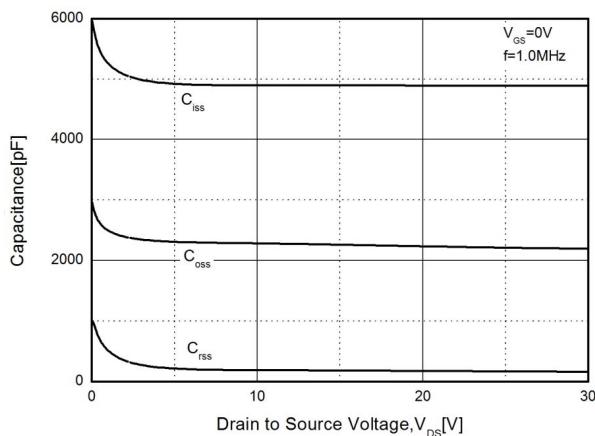


Figure5. Capacitance Characteristics

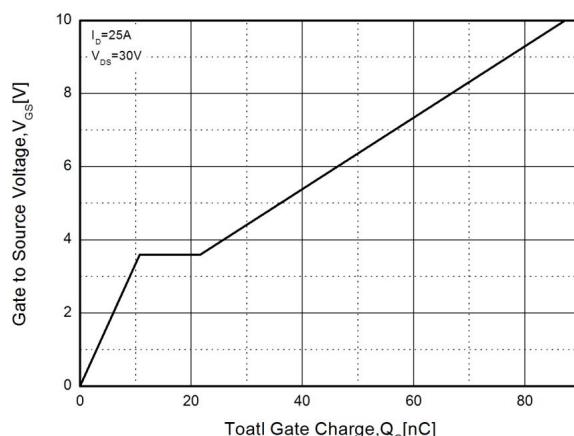


Figure6. Gate Charge

Typical Performance Characteristics (cont.)

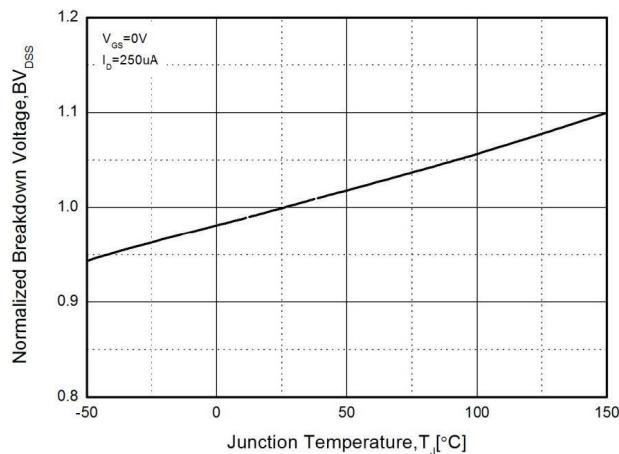


Figure7. Normalized Breakdown Voltage vs. Temperature

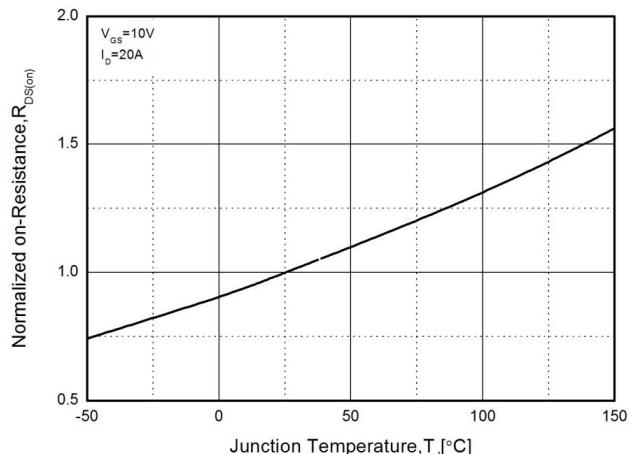


Figure8. Normalized on Resistance vs. Temperature

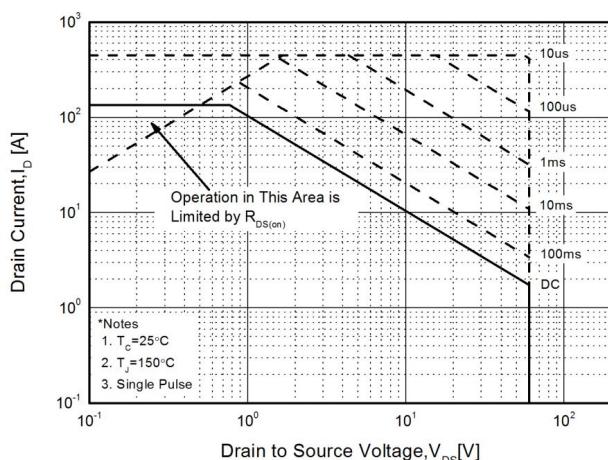


Figure9. Safe Operation Area

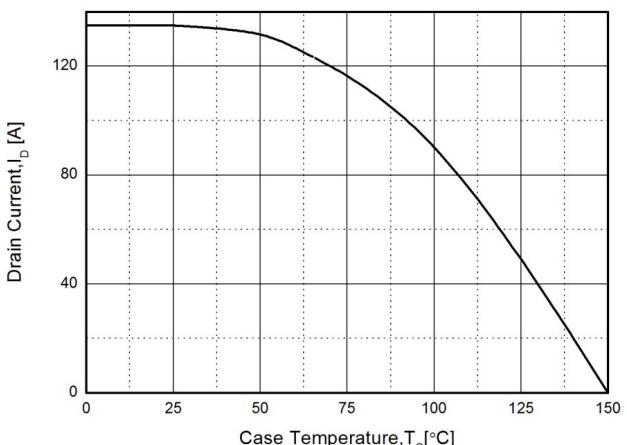


Figure10. Drain Current vs. Case Temperature

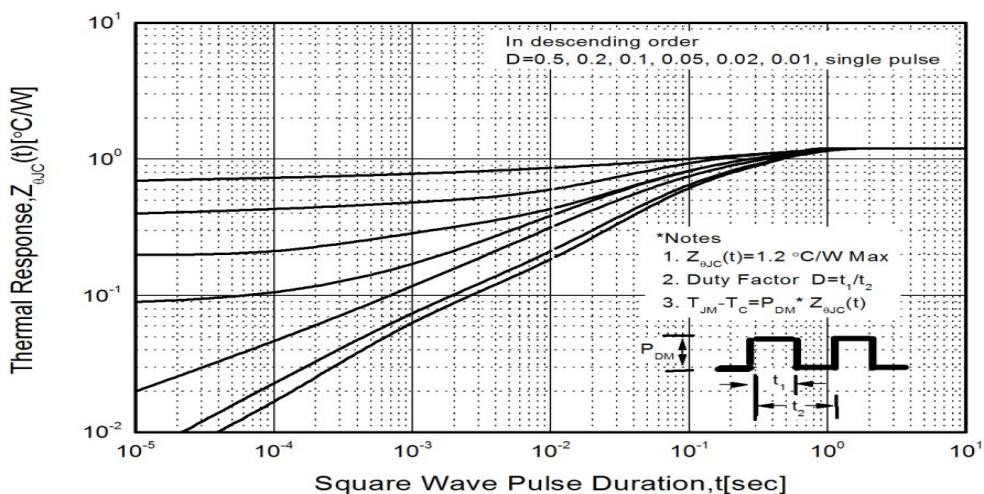
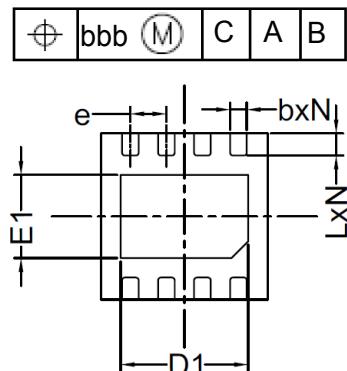
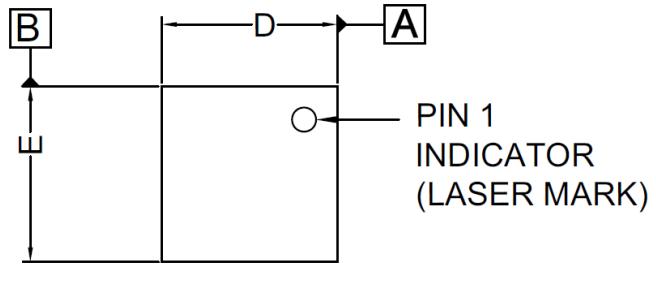


Figure11. Transient Thermal Response Curve

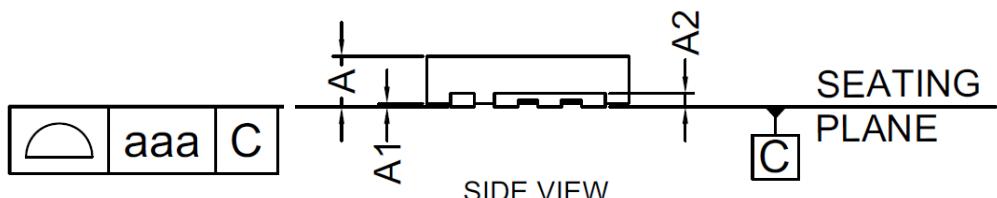
PDFN3.3*3.3-8L PACKAGE OUTLINE DRAWING



BOTTOM VIEW



TOP VIEW



SIDE VIEW

UNITS OF MEASURE=MILLIMETER

Symbol	Min	TYP	MAX
A	0.70	0.75	0.80
A1	0.00	0.02	0.05
A2		0.203	
b	0.25	0.30	0.35
D	2.924	3.00	3.076
D1	2.20	2.30	2.40
E	2.924	3.00	3.076
E1	1.40	1.50	1.60
e		0.65BSC	
L	0.35	0.40	0.45
K	0.20	-	
N		8	
aaa		0.08	
bbb		0.10	